

abstract
(Counterpart of reference(1))

SEMICONDUCTOR MEMORY DEVICE AND MEMORY DEVICE USING SAME

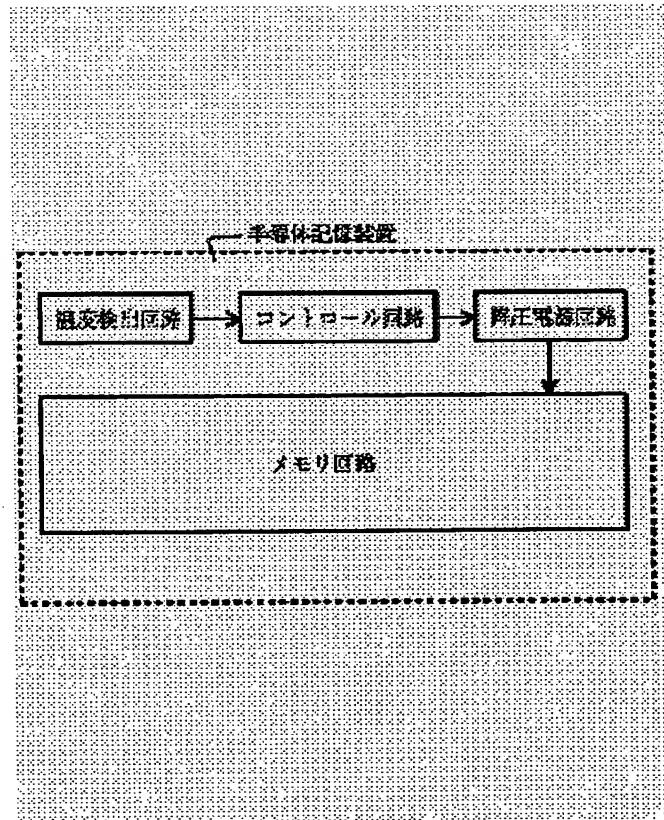
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Abstract of JP6085159

PURPOSE: To provide a new semiconductor memory device having a temperature limiting function and an easy to handle memory device which maintains a specified operation speed as well, embodying a higher density assembly.

CONSTITUTION: A step-down circuit is installed on a memory circuit whose operation speed is virtually rated in conformity with the electric current flowing in an MOSFET where the step-down circuit is designed to switch over operating voltage to a small voltage in terms of an absolute value based on a temperature detection circuit and a control signal transmitted from the detection output or outside. These semiconductor memory device are laminated and assembled while the step-down circuit is controlled by means of temperature detection signals of the circuit itself and temperature detection signals formed with other laminated memory devices, thereby reducing the operating voltage in terms of an absolute value.



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